SLOVENSKI STANDARD
oSIST prEN IEC 63567-4:2026

01-julij-2026

Polprevodniški elementi - Vrednotenje učinkovitosti komponent za obdelavo polprevodnikov in opreme za pregledovanje - 4. del: Metode ocenjevanja dimenzijske natančnosti laserskega razreza

Semiconductor devices - Performance evaluation of semiconductor processing components and inspection equipment - Part 4: Evaluation methods for dimensional accuracy of laser dicing process

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ICS:

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47/3011/CDV

COMMITTEE DRAFT FOR VOTE (CDV)

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IEC TC 47 : SEMICONDUCTOR DEVICES	
SECRETARIAT: Korea, Republic of	SECRETARY: Mr Cheolung Cha
OF INTEREST TO THE FOLLOWING COMMITTEES:	HORIZONTAL FUNCTION(S):
ASPECTS CONCERNED:	
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TITLE:

Semiconductor devices - Performance evaluation of semiconductor processing components and inspection equipment - Part 4: Evaluation methods for dimensional accuracy of laser dicing process

PROPOSED STABILITY DATE: 2029

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CONTENTS

FOREWORD 4
INTRODUCTION 5
1 Scope 6
2 Normative references 6
3 Terms and definitions 6
4 Procedures of laser dicing 7
4.1 Laser scribing 7
4.2 Backside grinding 7
4.3 Die separation 7
5 Die separation for test 7
5.1 Wafer selection 7
5.2 Test specimen 8
6 Test items for dimensional accuracy 8
6.1 Straightness 8
6.1.1 Measurement setup 8
6.1.2 Evaluation of straightness 8
5.2 Sidewall quality 9
6.2.1 Measurement setup 9
6.2.2 Evaluation of taper 10
6.2.3 Evaluation of sidewall flatness 10
6.3 Chipping 11
6.3.1 Measurement setup 11
6.3.2 Evaluation of chipping 11
7 Test report 12
7.1 Wafer specification 12
7.2 Laser dicing process parameters 12
7.3 Measurement conditions 12
7.4 Dimensional accuracy evaluation 12
Annex A (informative) Market relevance for the need of the standard 13
Annex B (informative) An example for the test report 14
B.1 Test specimen 15
B.2 Straightness evaluation 15
B.3 Taper evaluation 15
B.4 Sidewall quality evaluation 16
Bibliography 17

Figure 1 – Schematic for typical procedures of the laser dicing process 7
Figure 2 – Schematic of the test specimens in the diced wafer 8
Figure 3 – Top view of desired cutting line and actual cutting line 9
Figure 4 – Evaluation of straightness and offset 9
Figure 5 – Evaluation of taper 10
Figure 6 – Evaluation of sidewall flatness 10
Figure 7 – Evaluation of chipping 11
Figure A.1 – Evolution of die singulation process of silicon wafer in semiconductor industry 13

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Figure B.1 – Test specimen location 15
Figure B.2 – An optical microscope image for straightness evaluation 15
Figure B.3 – A scanning electron microscope image for taper evaluation 15
Figure B.4 – A scanning electron microscope image for sidewall quality evaluation 16

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

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SEMICONDUCTOR DEVICES – PERFORMANCE EVALUATION OF SEMICONDUCTOR PROCESSING COMPONENTS AND INSPECTION EQUIPMENT -

Part 4: Evaluation methods for dimensional accuracy of laser dicing process

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The text of this International Standard is based on the following documents:

Draft	Report on voting
XX/XX/FDIS	XX/XX/RVD

Full information on the voting for its approval can be found in the report on voting indicated in the above table.

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106 This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in
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